Interaction between point defects, extended defects and impurities in the Si-SiO2 system during the process of its formation

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; Mellikov, Enn Thin solid films 2004 / 1/2, p. 53-57 : ill

Interaction between point defects, extended defects and impurities in the Si-SiO2 system during the process of its formation

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn**; **Kauk, Marit** Materials science and engineering : B 2004 / p. 295-298 : ill